

General Description

The WST6401 is the highest performance trench P-ch MOSFET with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the small power switching and load switch applications.

The WST6401 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent C_{dv/dt} effect decline
- Green Device Available

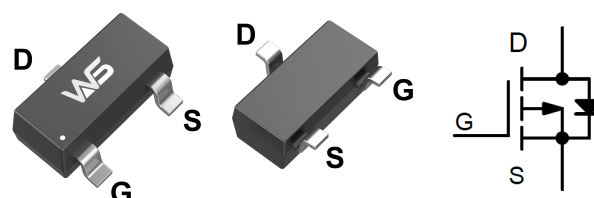
Product Summary

BVDSS	R _{DS(on)}	I _D
-20V	135mΩ	-2.5A

Applications

- High Frequency Point-of-Load Synchronous Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23N Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D @T _c =25°C	Continuous Drain Current, V _{GS} @ -4.5V ¹	-2.5	A
I _D @T _c =70°C	Continuous Drain Current, V _{GS} @ -4.5V ¹	-1.9	A
I _{DM}	Pulsed Drain Current ²	-10	A
P _D @T _A =25°C	Total Power Dissipation ³	0.7	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	178	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	80	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.016	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-2A	---	135	165	mΩ
		V _{GS} =-2.5V, I _D =-1A	---	150	186	
		V _{GS} =-1.8V, I _D =-1.5A	---	250	355	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.5	-0.7	-1.2	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	3.97	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±8V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-2A	---	.	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	13.1	---	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-2A	---	3.0	---	nC
Q _{gs}	Gate-Source Charge		---	0.5	---	
Q _{gd}	Gate-Drain Charge		---	0.8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-15V, V _{GS} =-4.5V, R _G =3.0Ω I _D =-2A	---	10	---	ns
T _r	Rise Time		---	5.0	---	
T _{d(off)}	Turn-Off Delay Time		---	21	---	
T _f	Fall Time		---	7	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	290	---	pF
C _{oss}	Output Capacitance		---	60	---	
C _{rss}	Reverse Transfer Capacitance		---	34	---	

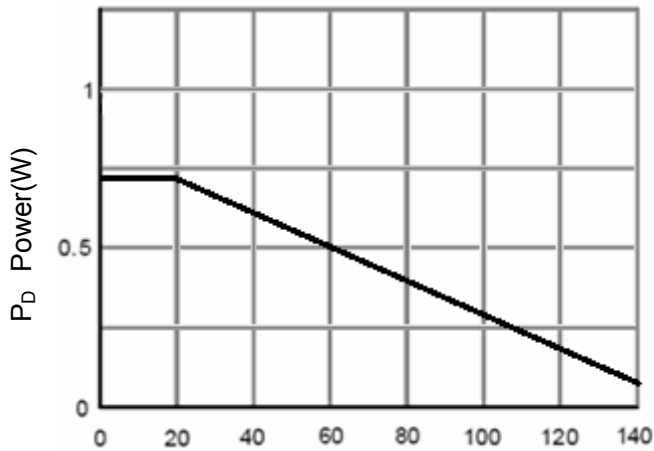
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-2.5	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	-10	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

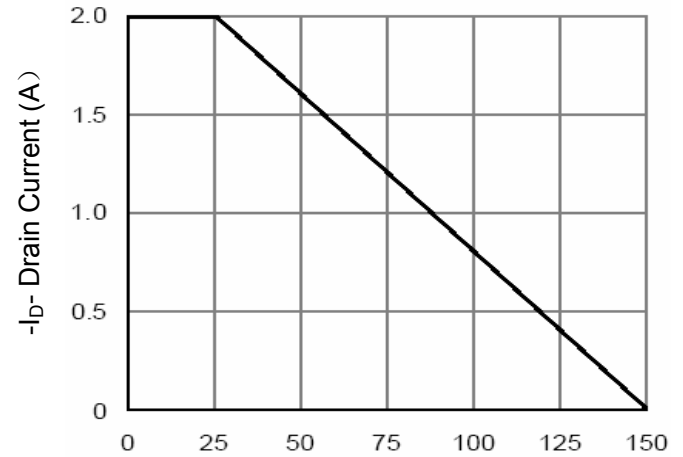
Notes:

- 1、Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2、Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3、Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
- 4、Guaranteed by design, not subject to production

Typical Characteristics



T_J-Junction Temperature(°C)
Figure 1 Power Dissipation



T_J-Junction Temperature(°C)
Figure 2 Drain Current

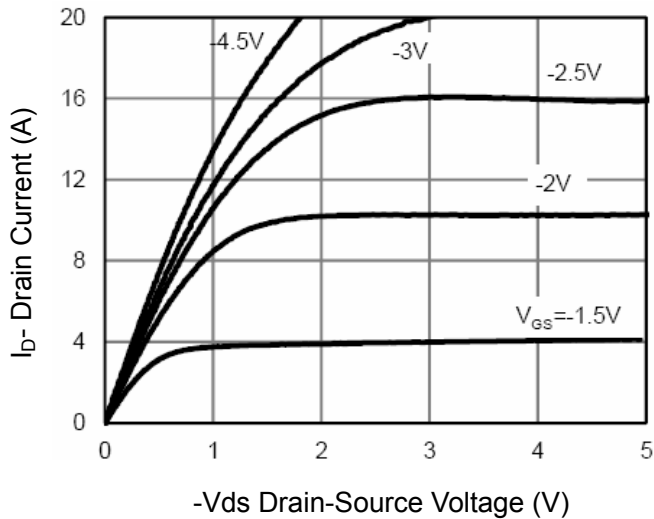


Figure 3 Output Characteristics

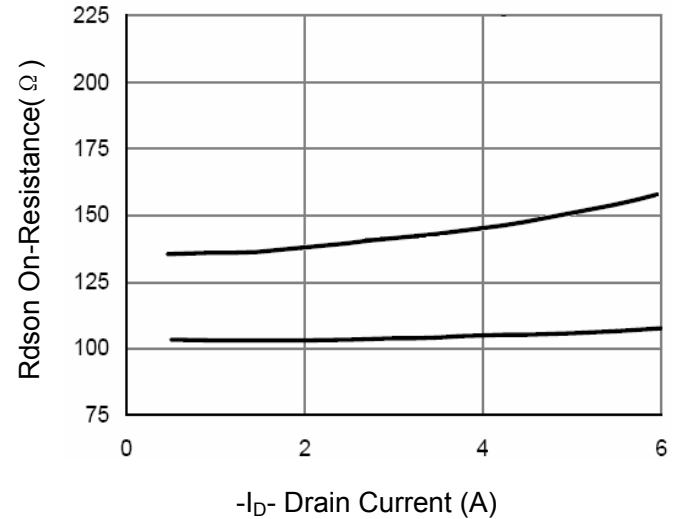


Figure 4 Drain-Source On-Resistance

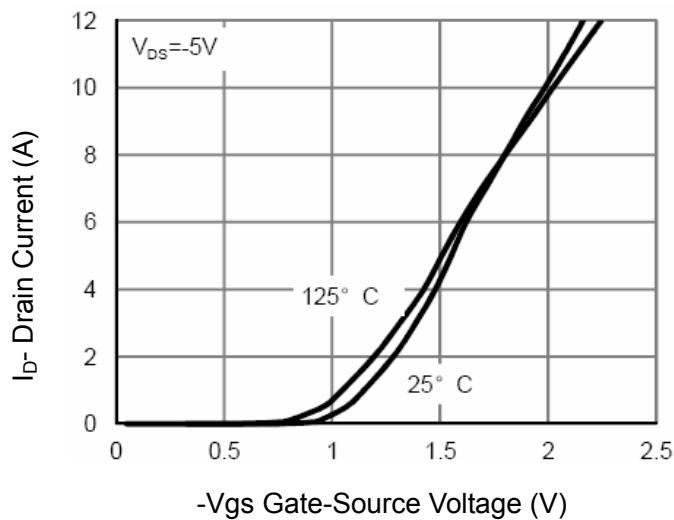


Figure 5 Transfer Characteristics

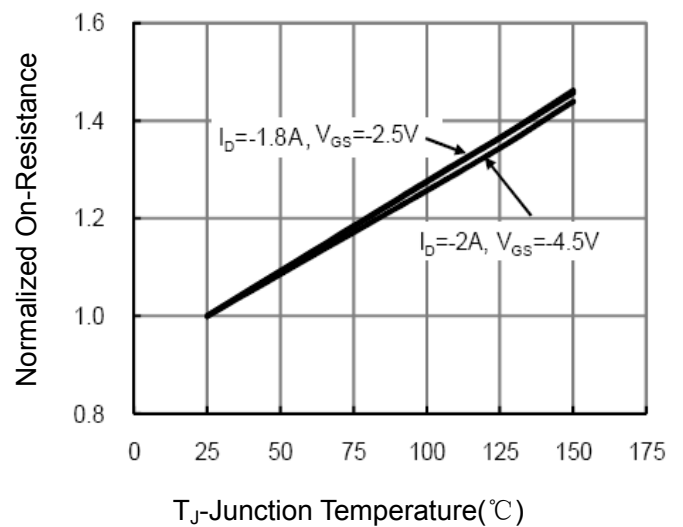


Figure 6 Drain-Source On-Resistance

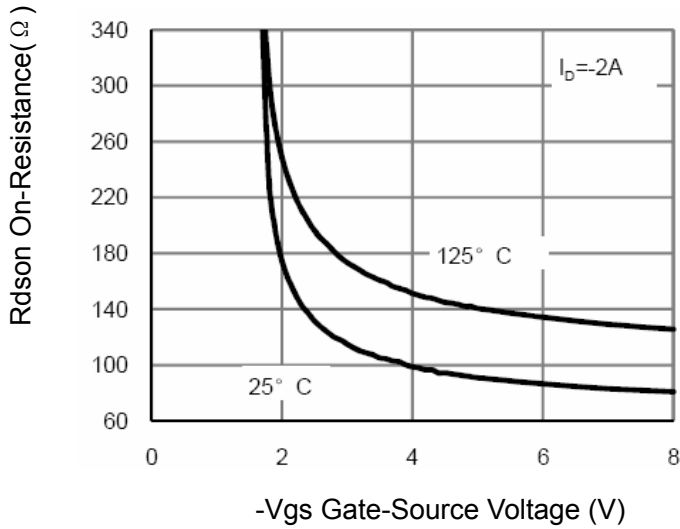


Figure 7 Rdson vs Vgs

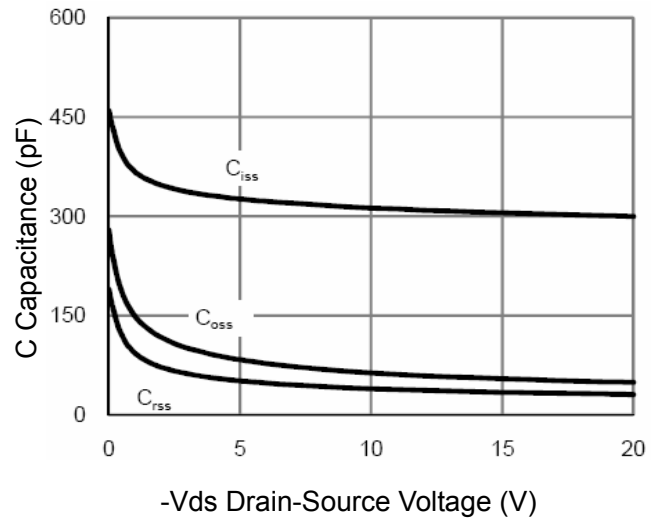


Figure 8 Capacitance vs Vds

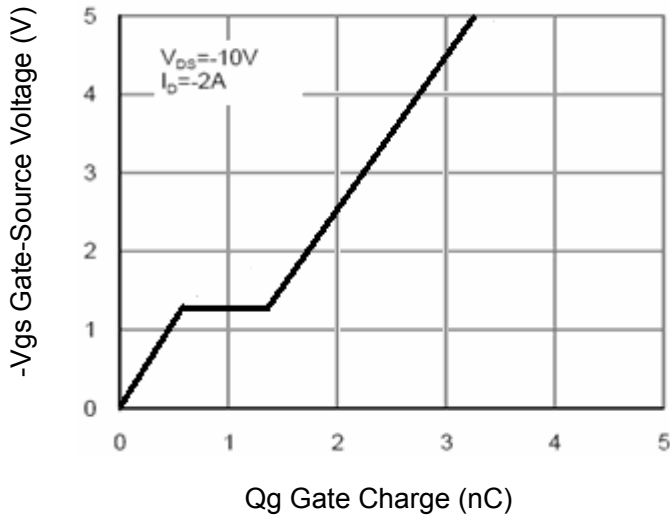


Figure 9 Gate Charge

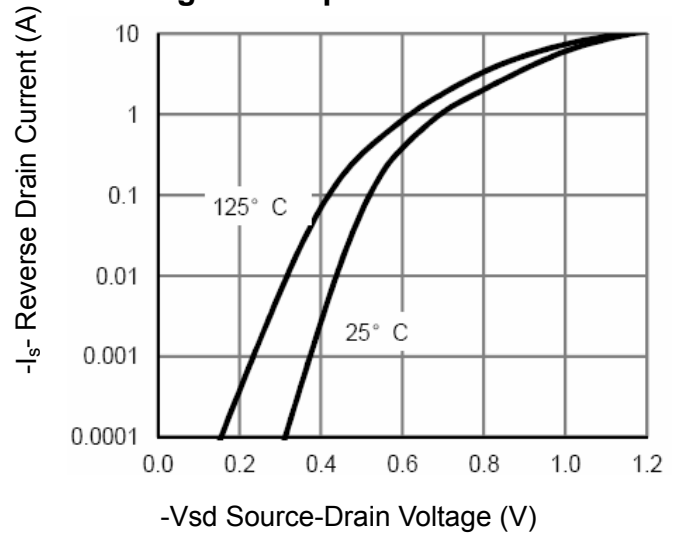


Figure 10 Source- Drain Diode Forward

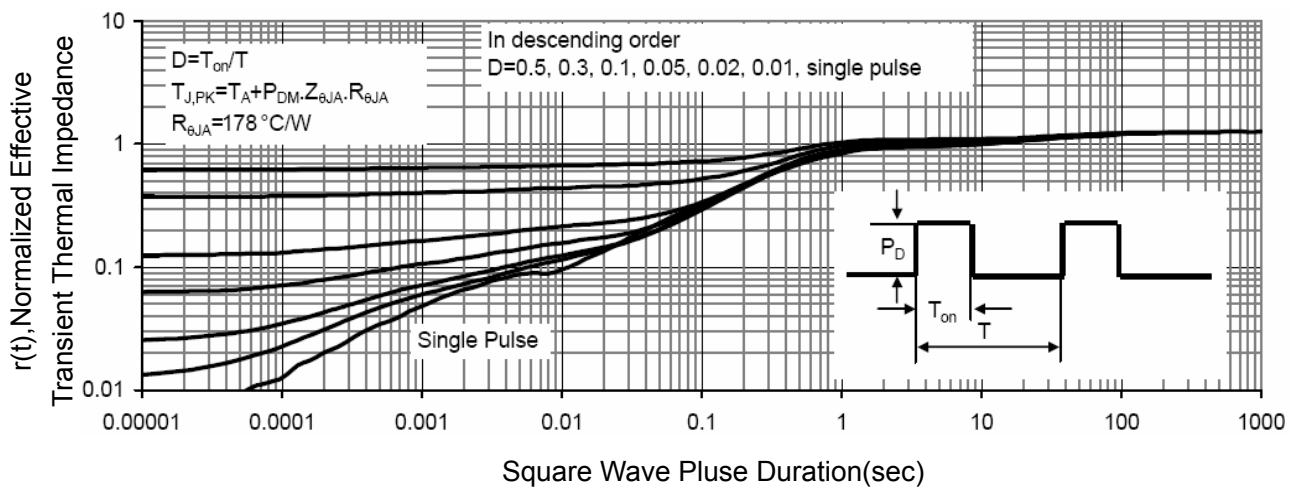


Figure 11 Normalized Maximum Transient Thermal Impedance

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